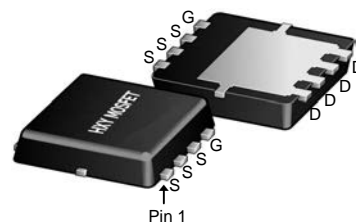




Description

The HAM7440N uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



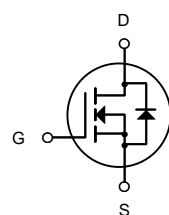
DFN5X6-8L

General Features

$V_{DS} = 40V$ $I_D = 50A$
 $R_{DS(ON)} < 14m\Omega$ $V_{GS} = 10V$

Application

Battery protection
Load switch
Uninterruptible power supply



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
HAM7440N	DFN5X6-8L	HXY MOSFET	5000

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	50	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	38	A
I_{DM}	Pulsed Drain Current ²	160	A
EAS	Single Pulse Avalanche Energy ³	50	mJ
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 175	$^\circ C$



Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	1.76	°C/W
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Electrical Characteristics ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	40	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250μA	1	1.6	2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =30A	-	11	14	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V,I _D =20A	30	-	-	S
Dynamic Characteristics ^(Note4)						
Input Capacitance	C _{Iss}	V _{DS} =25V,V _{GS} =0V, F=1.0MHz	-	1540	-	PF
Output Capacitance	C _{Oss}		-	171	-	PF
Reverse Transfer Capacitance	C _{rSS}		-	115	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =20V,I _D =20A,R _L =1Ω V _{GS} =10V,R _{GEN} =3Ω	-	5.0	-	nS
Turn-on Rise Time	t _r		-	24	-	nS
Turn-Off Delay Time	t _{d(off)}		-	38	-	nS
Turn-Off Fall Time	t _f		-	12	-	nS
Total Gate Charge	Q _g	V _{DS} =30V,I _D =30A, V _{GS} =10V	-	24	-	nC
Gate-Source Charge	Q _{gs}		-	5.9	-	nC
Gate-Drain Charge	Q _{gd}		-	3.6	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V _{SD}	V _{GS} =0V,I _S =30A	-	-	1.2	V
Diode Forward Current ^(Note 2)	I _S		-	-	48	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F =30A di/dt = 100A/μs ^(Note3)	-	9		nS
Reverse Recovery Charge	Q _{rr}		-	15		nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

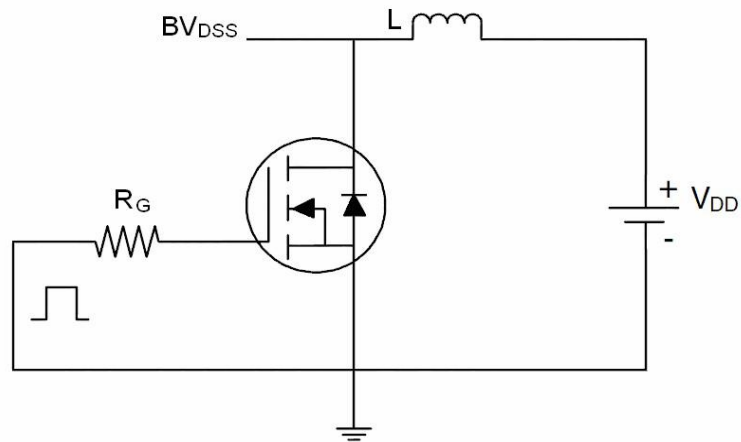
Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. E_{AS} condition: $T_J=25^{\circ}\text{C}, V_{DD}=30V, V_G=10V, L=0.5mH, R_g=25\Omega$

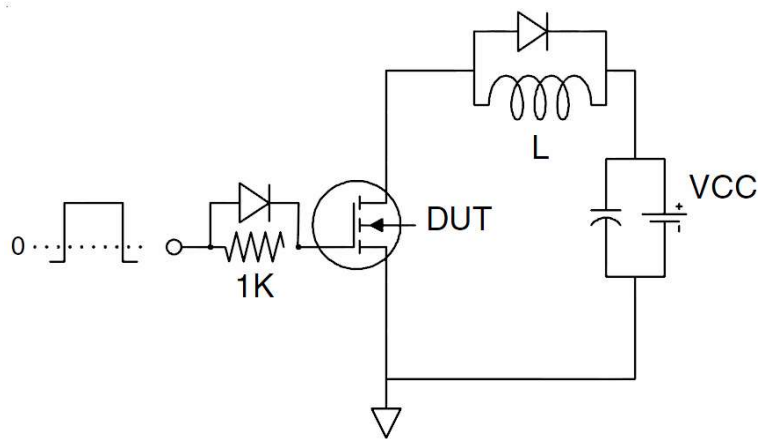


Test circuit

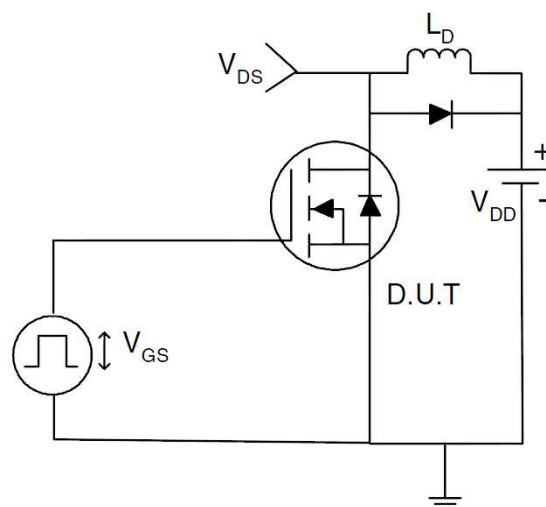
1) E_{AS} test Circuits



2) Gate charge test Circuit

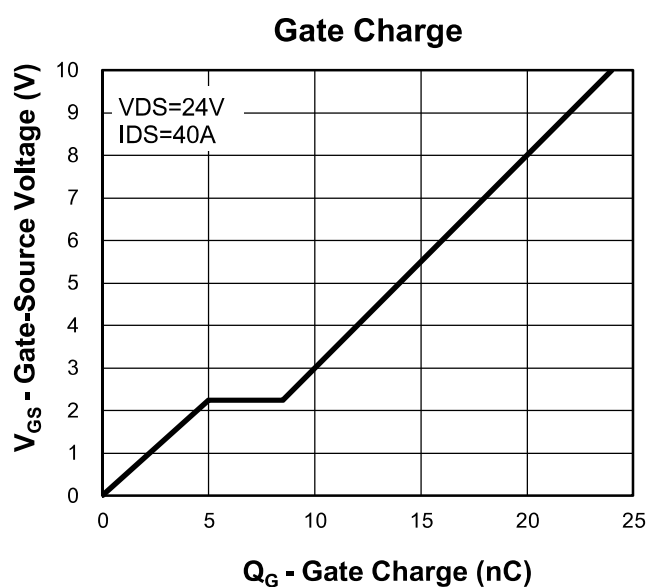
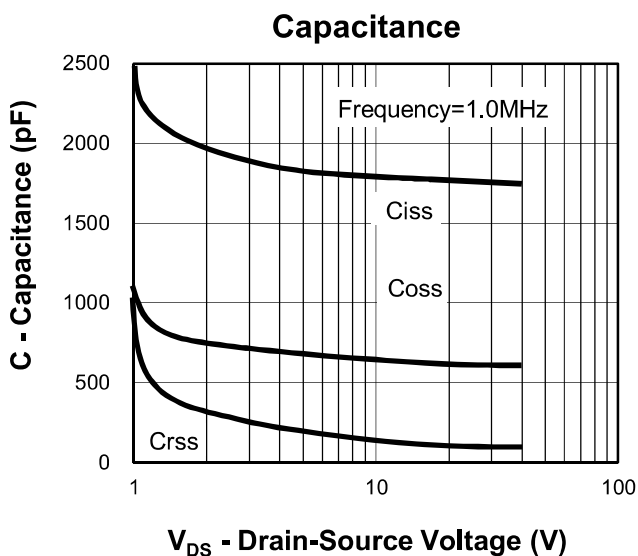
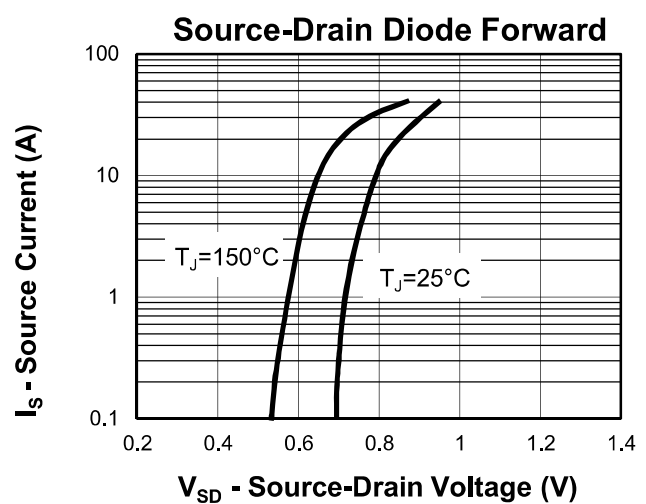
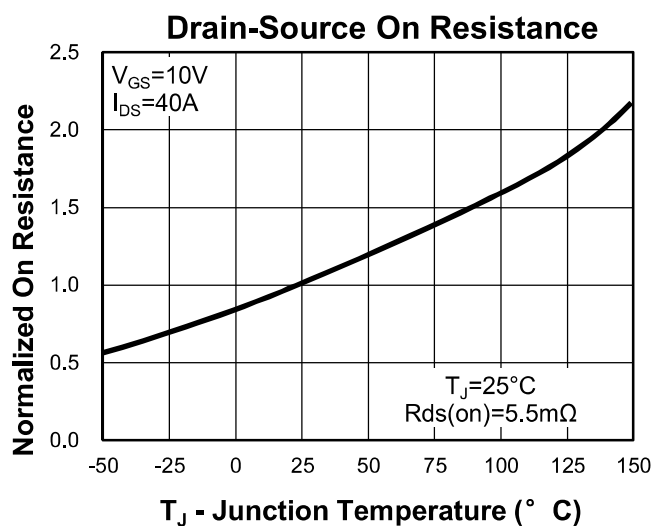
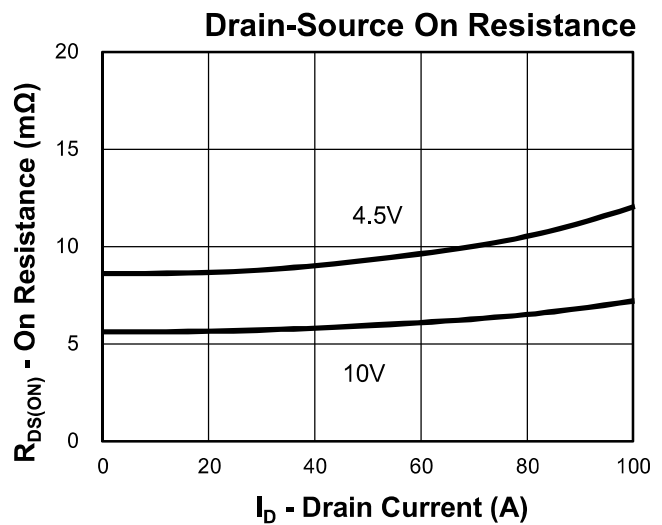
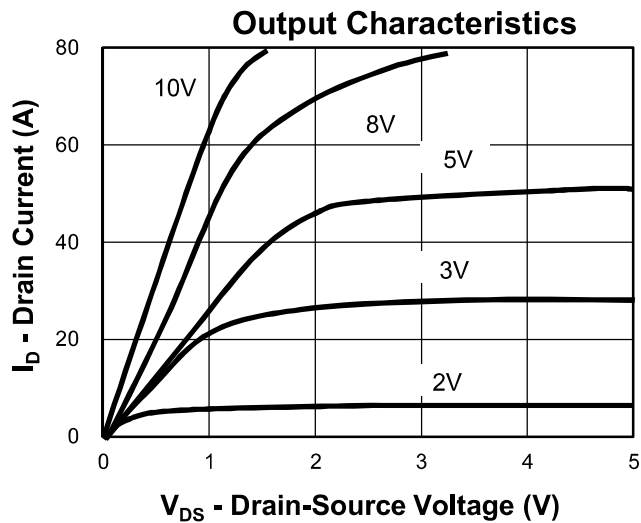


3) Switch Time Test Circuit



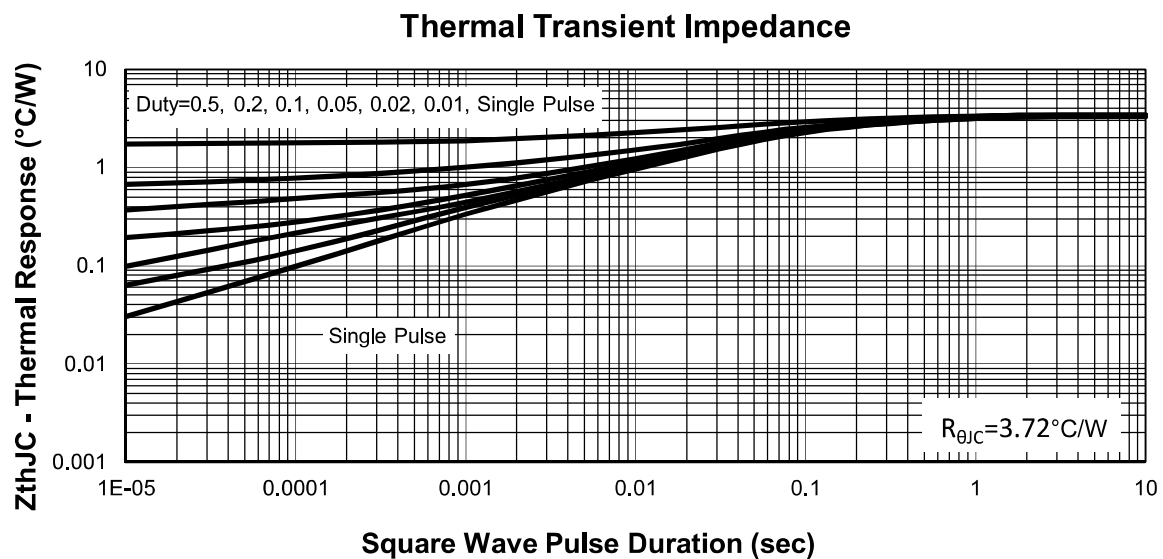
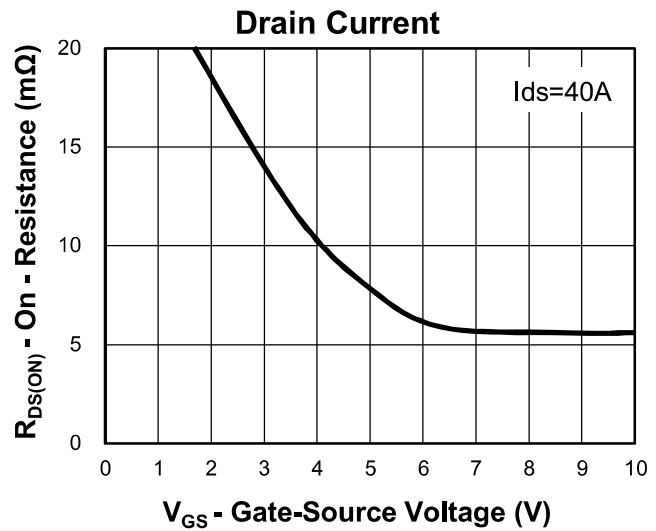
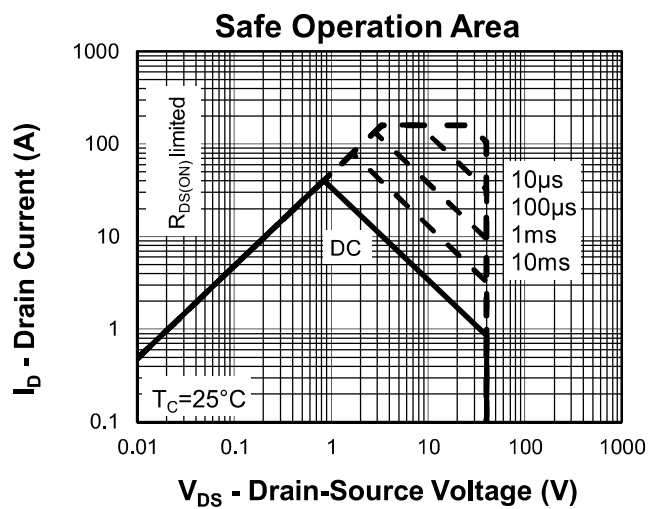
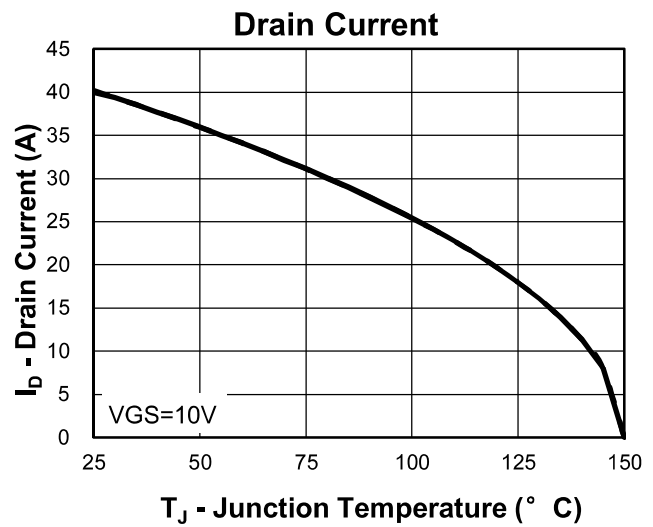
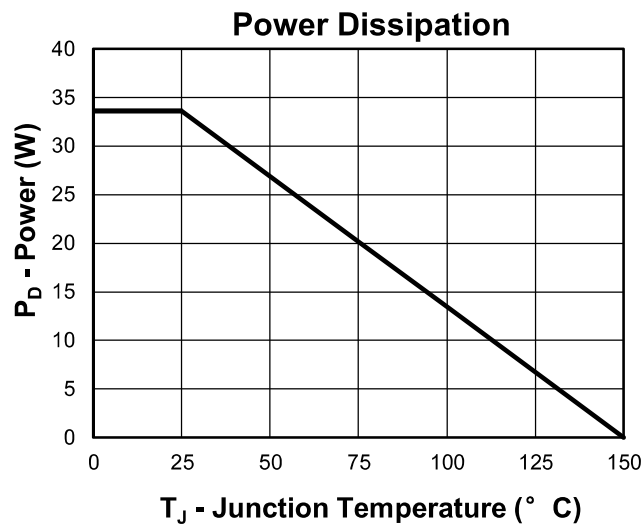


Typical Characteristics



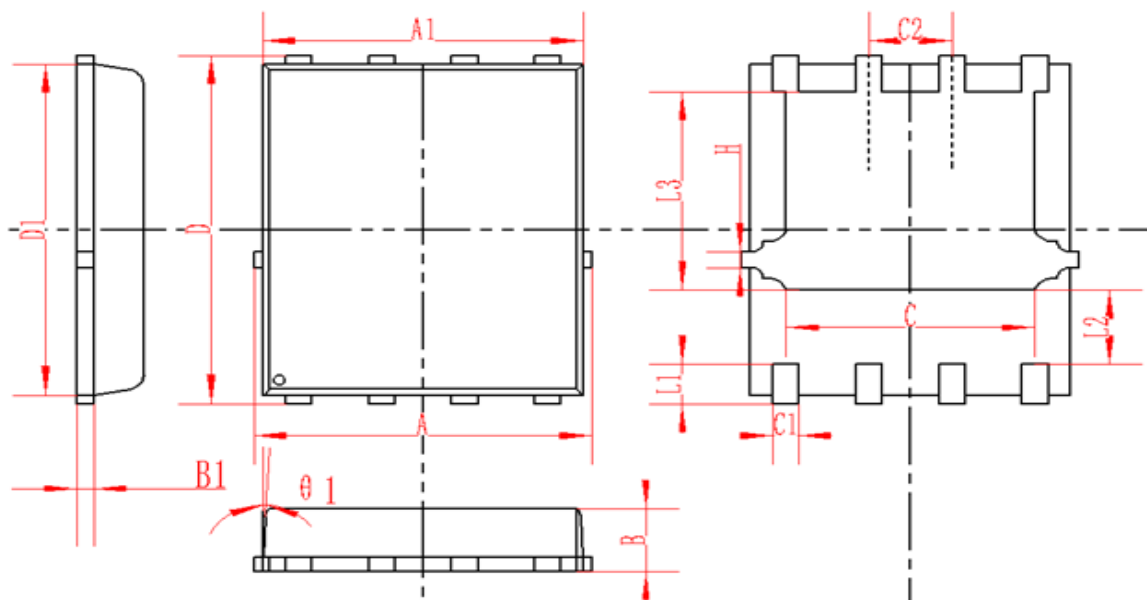


Typical Characteristics





DFN5X6-8L Package Information



SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.95	5	5.05	0.195	0.197	0.199
A1	4.82	4.9	4.98	0.190	0.193	0.196
D	5.98	6	6.02	0.235	0.236	0.237
D1	5.67	5.75	5.83	0.223	0.226	0.230
B	0.9	0.95	1	0.035	0.037	0.039
B1	0.254REF			0.010REF		
C	3.95	4	4.05	0.156	0.157	0.159
C1	0.35	0.4	0.45	0.014	0.016	0.018
C2	1.27TYP			0.5TYP		
θ1	8°	10°	12°	8°	10°	12°
L1	0.63	0.64	0.65	0.025	0.025	0.026
L2	1.2	1.3	1.4	0.047	0.051	0.055
L3	3.415	3.42	3.425	0.134	0.135	0.135
H	0.24	0.25	0.26	0.009	0.010	0.010



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